## In-situ measurement of Raman scattering and AFM during laser-heated ACCVD growth process of SWNTs

OShohei Chiashi, Yoichi Murakami, Yuhei Miyauchi and Shigeo Maruyama

Department of Mechanical Engineering, The University of Tokyo 7-3-1 Hongo, Bunkyo-ku, Tokyo 113-8656, Japan

We have built an atomic force microscope (AFM) with Raman scattering measurement capabilities and succeeded in synthesizing SWNTs on the AFM sample stage [1] using alcohol catalytic CVD method [2].

In this experimental apparatus, in-situ measurement of Raman scattering and AFM were performed while **SWNTs** were using "laser-heated" synthesized by cold-wall ACCVD method. Mo/Co metal particles, which were directly loaded on the silicon substrate [3], was used as the catalyst and CW-Ar-ion laser (488.0 nm, 50.0 mW) as the heating was used and Raman shows in-situ excitation. Fig. 1 the measurement of the intensity of the G-band



Fig. 1 . In-situ measurement of the Raman scattering intensity from (a) SWNTs and (b) the silicon substrate during the laser-heated CVD process. The sample temperature (c) was calculated from the temperature dependence of Raman shift from the silicon peak (520 cm<sup>-1</sup> at 300 K).

(a) and Raman scattering peak from the silicon substrate (b) during the CVD process. The sample temperature (c) was calculated from the temperature dependence of Raman shift of the silicon peak [4]. About 40 s after the supply of the ethanol gas (0.1 Torr), the G-band appeared at 1570 cm<sup>-1</sup>. The G-band intensity increased with time, but the intensity increase stopped about 4 min after the appearance of the G-band, which indicated the inactivation of the metal catalyst particles and the stop of the SWNTs growth. In the waiting time for the G-band appearance, SWNTs could not be found by in-situ AFM measurement.

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Corresponding Author: Shigeo Maruyama E-mail: maruyama@photon.t.u-tokyo.ac.jp Tel&Fax: +81-3-5800-6983